

General Purpose Transistor Medium Power, NPN 80 V, 1 A

BCP56M

The BCP56MTW is designed for general purpose amplifier applications. It is housed in DFN2020–3 offering superior thermal performance. The transistor is ideal for medium–power surface mount applications where board space and reliability are at a premium.

Specification Features

- Wettable Flank Package for Optimal Automated Optical Inspection (AOI)
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Collector-Base Voltage	V _{CBO}	100	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous (Note 1)	I _C	1.0	Α
Collector Current - Peak (Note 1)	I _{CM}	2.0	Α

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

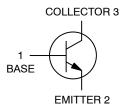
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Power Dissipation (Note 2) @ T _A = 25°C Derate above 25°C	P _D	1.5	V
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	78	°C/W
Total Power Dissipation (Note 3) @ T _A = 25°C Derate above 25°C	P _D	875	mW
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	138	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

- 1. Reference SOA Curve
- 2. Surface-mounted on FR4 board using a 600 mm² pad area and 2 oz. Cu
- 3. Surface-mounted on FR4 board using a 100 mm² pad area and 2 oz. Cu

1





MARKING DIAGRAM



6M = Specific Device Code M = Date Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

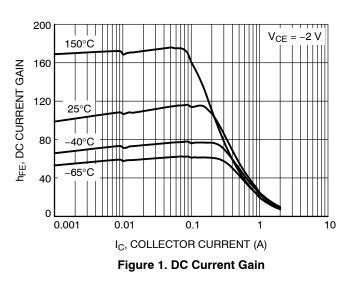
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	•
Collector-Emitter Breakdown Voltage (I _C = 1 mA, I _B = 0 A)	V _{(BR)CEO}	80	-	-	V
Collector-Base Breakdown Voltage ($I_C = 100 \mu A$, $I_E = 0 A$)	V _{(BR)CBO}	100	-	-	V
Emitter-Base Breakdown Voltage ($I_E = 10 \mu A, I_C = 0$)	V _{(BR)EBO}	5	-	-	V
Collector-Base Cutoff Current (V _{CB} = 30 V, I _E = 0)	I _{CBO}	=	-	100	nA
Emitter-Base Cutoff Current ($V_{EB} = 5 \text{ V}, I_{C} = 0$)	I _{EBO}	-	-	100	nA
ON CHARACTERISTICS (Note 4)			•	•	•
$\begin{array}{ll} \text{DC Current Gain} \\ \text{(I}_{\text{C}} = 5 \text{ mA, V}_{\text{CE}} = 2.0 \text{ V}) \\ \text{(I}_{\text{C}} = 150 \text{ mA, V}_{\text{CE}} = 2.0 \text{ V}) \\ \text{BCP56M} \\ \text{BCP5610M} \\ \text{BCP5616M} \\ \text{(I}_{\text{C}} = 500 \text{ mA, V}_{\text{CE}} = 2.0 \text{ V}) \\ \text{All Part Types} \end{array}$	h _{FE}	63 63 63 100 40	- - - -	- 250 160 250 -	
Collector-Emitter Saturation Voltage (I _C = 500 mA, I _B = 50 mA)	V _{CE(sat)}	=	-	0.50	V
Base-Emitter Saturation Voltage ($I_C = 500 \text{ mA}$, $I_B = 50 \text{ mA}$)	V _{BE(sat)}	-	-	2.0	V
Base-Emitter Turn-on Voltage (I _C = 500 mA, V _{CE} = 2.0 V)	V _{BE(on)}	_	-	1.0	V
SMALL SIGNAL CHARACTERISTICS			•	•	
Transition Frequency (I _C = 10 mA, V _{CE} = 5.0 V, f = 100 MHz)	f _T	-	140	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	65	-	pF
Input Capacitance (V _{EB} = -0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	130	-	pF
Input Impedance ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h _{ie}	-	4	-	k
Voltage Feedback Ratio ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h _{re}	-	0.4	-	X 10 ⁻⁴
Small–Signal Current Gain (I _C = –1.0 mAdc, V _{CE} = –10 Vdc, f = 1.0 kHz)	h _{fe}	-	135	-	-
Output Admittance (I _C = -1.0 mAdc, V _{CE} = -10 Vdc, f = 1.0 kHz)	H _{oe}	=	4	-	μmhos
Noise Figure (I _C = 0.2 mA, V_{CE} = 5.0 Vdc, R_S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	ı	1	-	dB
SWITCHING CHARACTERISTICS					
Delay Time (V _{CC} = 30 Vdc, I _C = 150 mA, I _{B1} = 15 mA)	t _d	=	20	-	ns
Rise Time (V _{CC} = 30 Vdc, I _C = 150 mA, I _{B1} = 15 mA)	t _r	=	20	-	ns
Storage Time (V_{CC} = 30 Vdc, I_{C} = 150 mA, I_{B1} = 15 mA, I_{B2} = 15 mA)	t _s	-	900	-	ns
Fall Time (V_{CC} = 30 Vdc, I_{C} = 150 mA, I_{B1} = 15 mA, I_{B2} = 15 mA)	t _f	-	110	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Condition: Pulse Width = $300 \mu s$, Duty Cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS



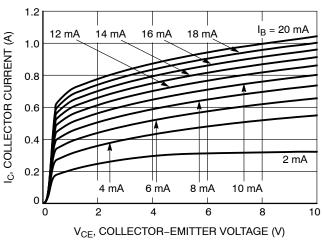


Figure 2. Collector Current vs. Collector Emitter Voltage

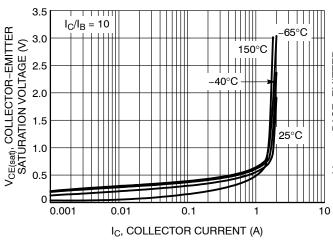


Figure 3. Collector Emitter Saturation Voltage vs. Collector Current

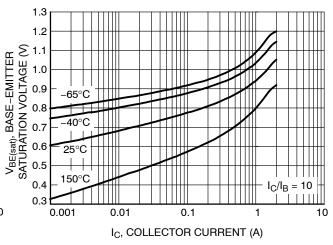


Figure 4. Base Emitter Saturation Voltage vs.
Collector Current

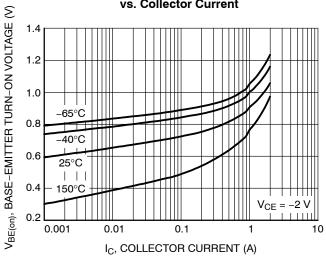


Figure 5. BCP53M, Base Emitter Turn-On Voltage vs. Collector Current V_{BE(on)}

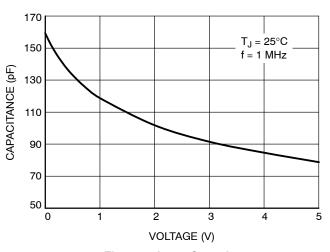


Figure 6. Input Capacitance

TYPICAL CHARACTERISTICS

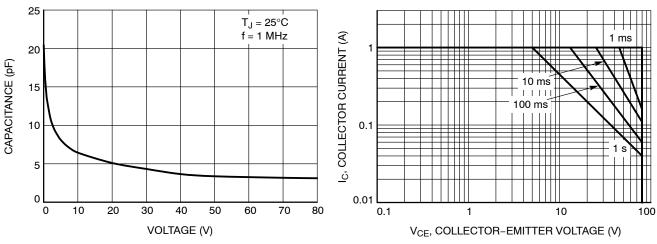


Figure 7. Output Capacitance

Figure 8. Safe Operating Area

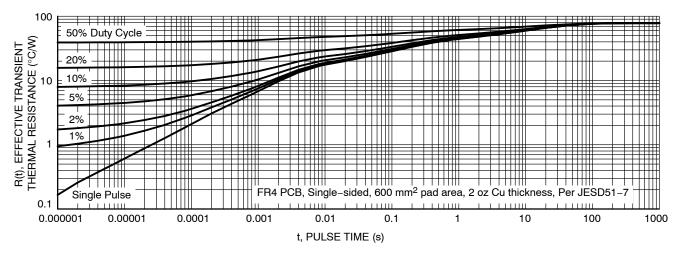


Figure 9. Transient Thermal Impedance from Junction-to-Ambient as a Function of Pulse Duration

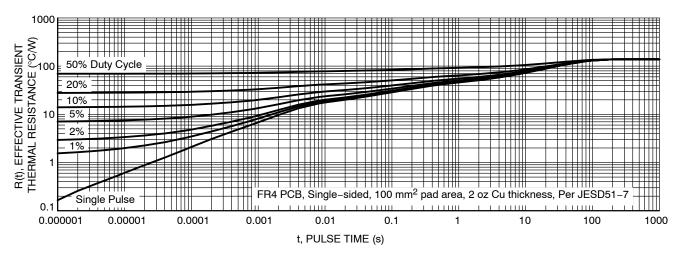


Figure 10. Transient Thermal Impedance from Junction-to-Ambient as a Function of Pulse Duration

ORDERING INFORMATION

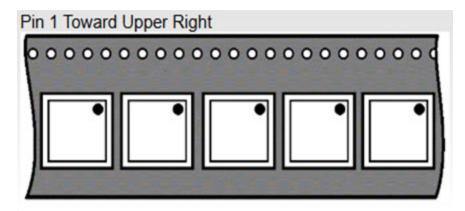
Device	Marking	Package	Shipping [†]		
BCP56MTWG	6M				
BCP5610MTWG	6N	WDFNW3 (Pb-Free)	2000 / Tapa ⁹ Paol		
BCP5616MTWG	6P				
NSVBCP56MTWG*	6M		3000 / Tape & Reel		
NSVBCP5610MTWG*	6N				
NSVBCP5616MTWG*	6P				

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Pin 1 Orientation in Tape and Reel

Direction of Feed





^{*}NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.





PIN A1 REFERENCE

△ 010 C



WDFNW3 2x2, 1.3P CASE 515AA ISSUE A

DATE 26 JUL 2022

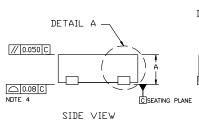
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30MM FORM THE TERMINAL TIP.
- 4. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.

A3-

-D1

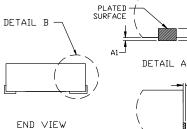
PLATED SURFACE



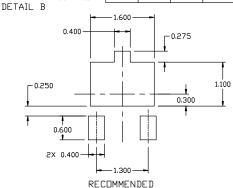
TOP VIEW

В

Ė



MILLIMETERS DIM MIN. N□M. MAX 0.70 0.75 0.80 Α A1 0.00 0.05 АЗ 0.20 REI 0.30 0.35 b 0.25 D 2.00 BSC D1 0.00 0.04 D2 1.40 1.50 1.60 2.00 BSC Ε E2 0.90 1.00 1.10 1.30 BSC е Κ 0.35 REF 0.35 0.40 0.45



GENERIC MARKING DIAGRAM*

BOTTOM VIEW



XX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

MDUNTING FOOTPRINT*

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON33309H	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	WDFNW3 2x2, 1.3P		PAGE 1 OF 1	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales